

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>c</sub> = +25°C (Note 5)
60V	4.1mΩ @ V <sub>GS</sub> = 10V	100A
	6.3mΩ @ V <sub>GS</sub> = 6V	81A
	7mΩ @ V <sub>GS</sub> = 4.5V	77A

## Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> – Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact_us) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

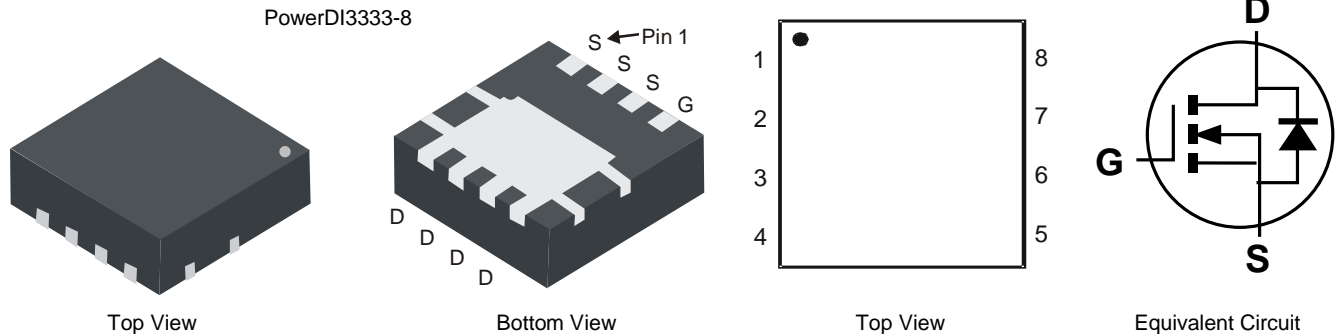
## Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Synchronous rectification
- Motor controls
- DC-DC converters
- Power management

## Mechanical Data

- Package: PowerDI<sup>®</sup>3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.034 grams (Approximate)



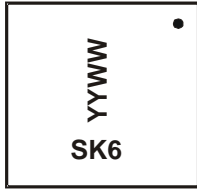
## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMT6005LFG-7	PowerDI3333-8	2,000	Tape & Reel
DMT6005LFG-13	PowerDI3333-8	3,000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.
  5. Limited by package.

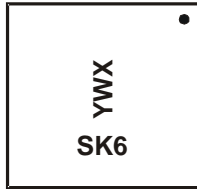
## Marking Information

Site 1:



SK6 = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 24 = 2024)  
 WW = Week Code (01 to 53)

Site 2:



SK6 = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 4 = 2024)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

Date Code Key

<b>Year</b>	2018	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
<b>Code</b>	8	-	4	5	6	7	8	9	0	1	2	3
<b>Week</b>	1-26			27-52				53				
<b>Code</b>	A-Z			a-z				z				
<b>Internal Code</b>	<b>Sun</b>	<b>Mon</b>	<b>Tue</b>	<b>Wed</b>	<b>Thu</b>	<b>Fri</b>	<b>Sat</b>					
<b>Code</b>	T	U	V	W	X	Y	Z					

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Notes 5 & 6) V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>C</sub> = +25°C 100	A
		T <sub>C</sub> = +70°C 80	
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>A</sub> = +25°C 18	A
		T <sub>A</sub> = +70°C 14	
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	400	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	400	A
Avalanche Current, L = 1mH	I <sub>AS</sub>	18.5	A
Avalanche Energy, L = 1mH	E <sub>AS</sub>	171	mJ

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 7)	P <sub>D</sub>	T <sub>A</sub> = +25°C	1.98
Thermal Resistance, Junction to Ambient (Note 7)		R <sub>θJA</sub>	63
Total Power Dissipation (Note 6)	P <sub>D</sub>	T <sub>C</sub> = +25°C	62.5
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	2.0
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
5. Limited by package.
  6. Thermal resistance from junction to soldering point (on the exposed drain pad).
  7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	3.1	4.1	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		—	3.6	6.3	mΩ	V <sub>GS</sub> = 6V, I <sub>D</sub> = 20A
		—	4.4	7	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	3150	—	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	1036	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	69	—		
Gate Resistance	R <sub>g</sub>	—	0.7	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	48.7	—	nC	V <sub>DD</sub> = 30V, I <sub>D</sub> = 50A
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	23.6	—		
Gate-Source Charge	Q <sub>gs</sub>	—	7.0	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	11.2	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	7.3	—	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V I <sub>D</sub> = 30A, R <sub>g</sub> = 3.3Ω
Turn-On Rise Time	t <sub>R</sub>	—	11.3	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	26.0	—		
Turn-Off Fall Time	t <sub>F</sub>	—	11.0	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	40.8	—	ns	I <sub>F</sub> = 30A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	51.5	—	nC	

Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.

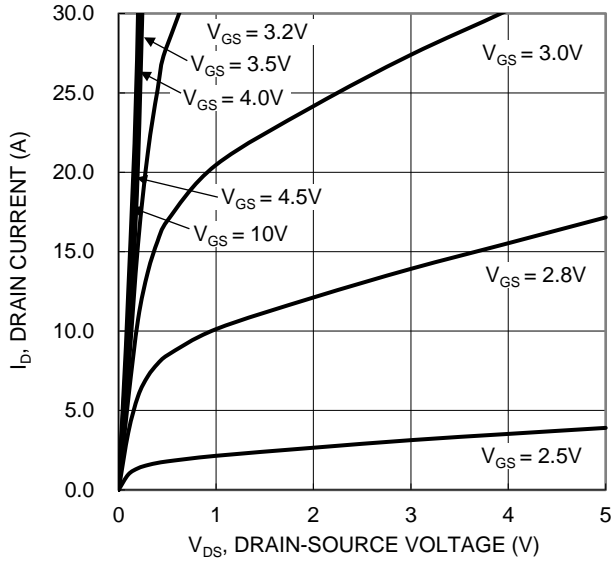


Figure 1. Typical Output Characteristic

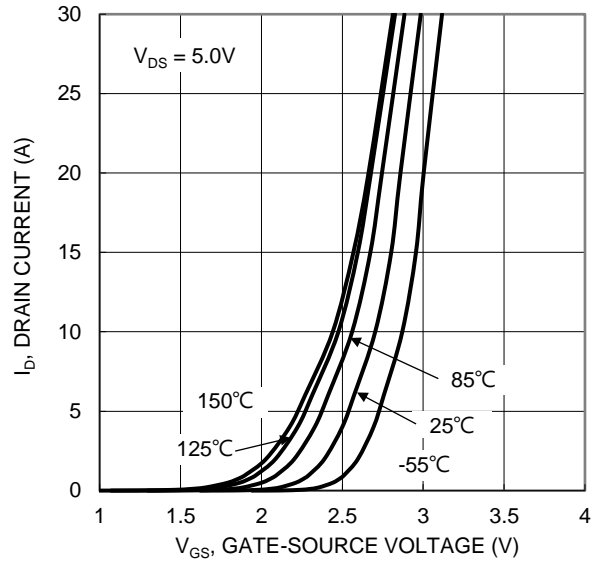


Figure 2. Typical Transfer Characteristic

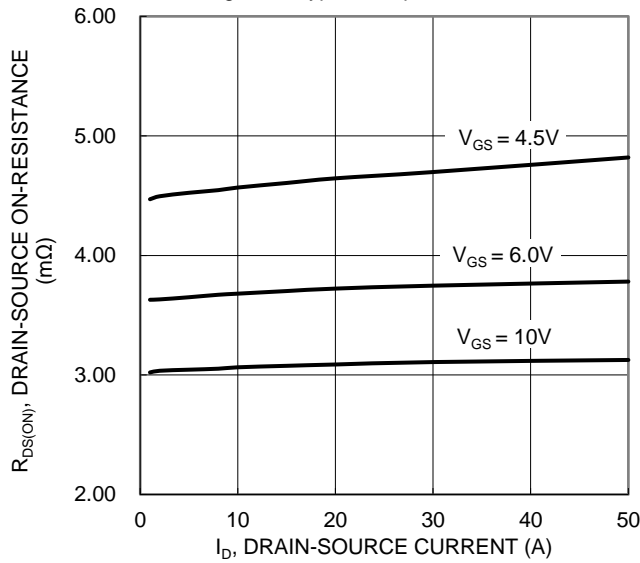


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

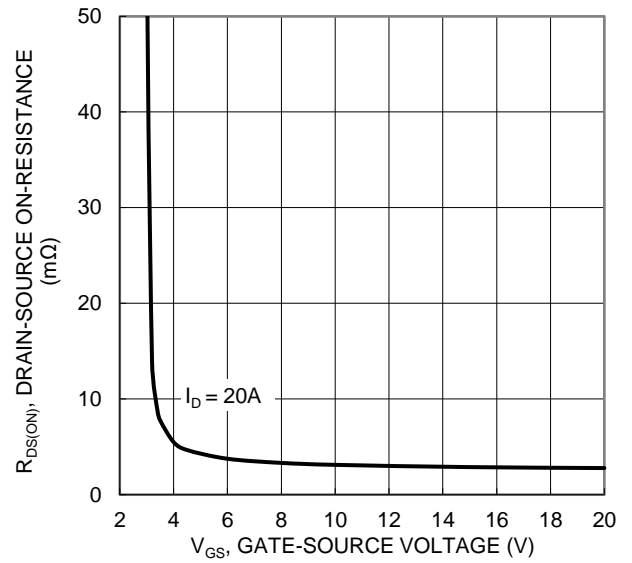


Figure 4. Typical Transfer Characteristic

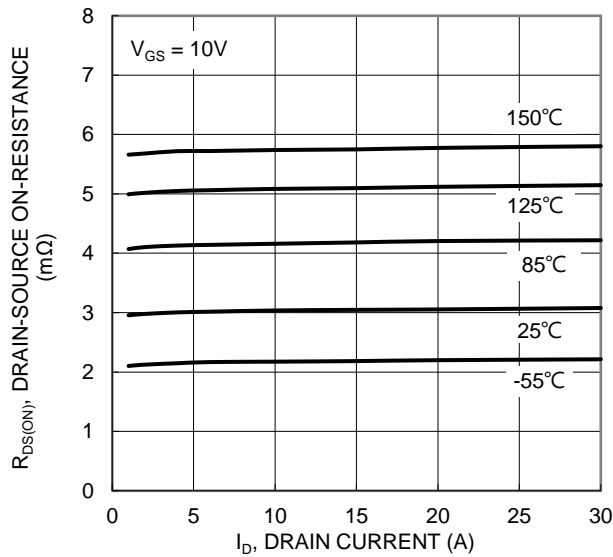


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

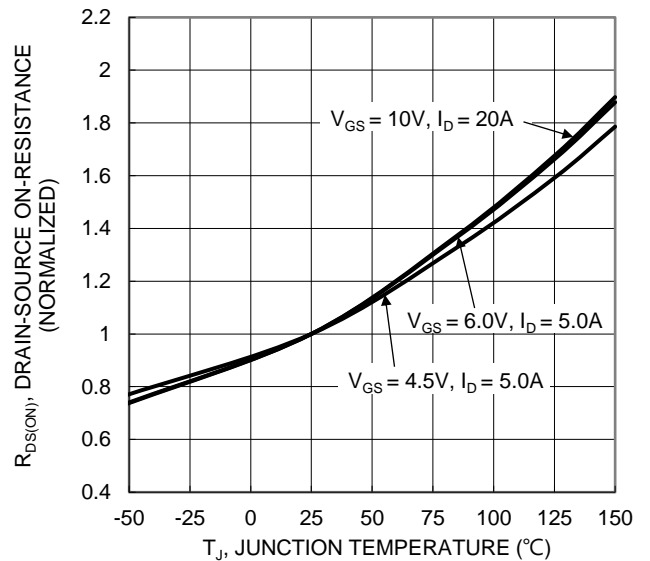


Figure 6. On-Resistance Variation with Temperature

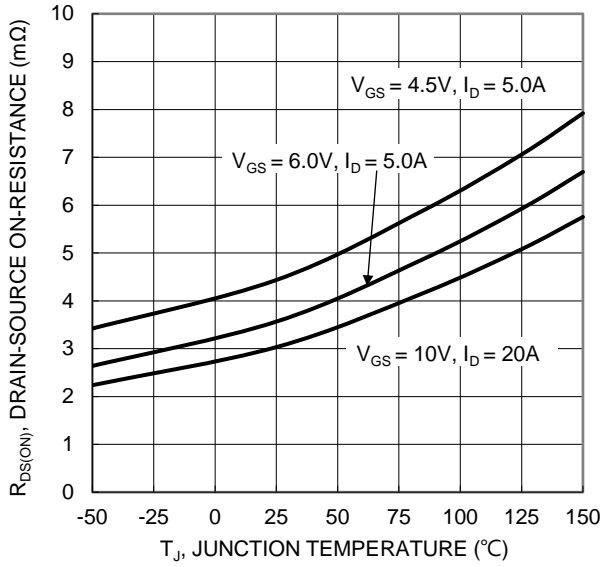


Figure 7. On-Resistance Variation with Temperature

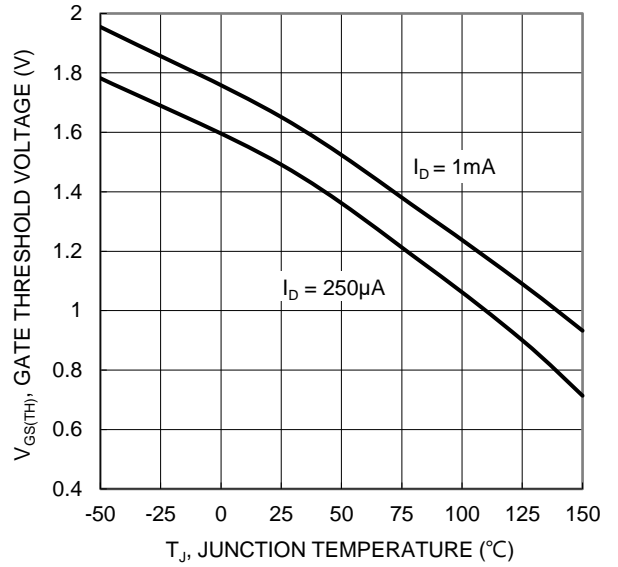


Figure 8. Gate Threshold Variation vs. Junction Temperature

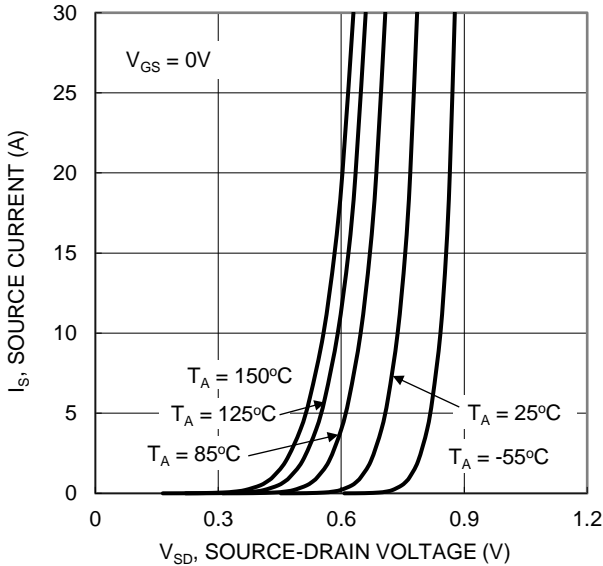


Figure 9. Diode Forward Voltage vs. Current

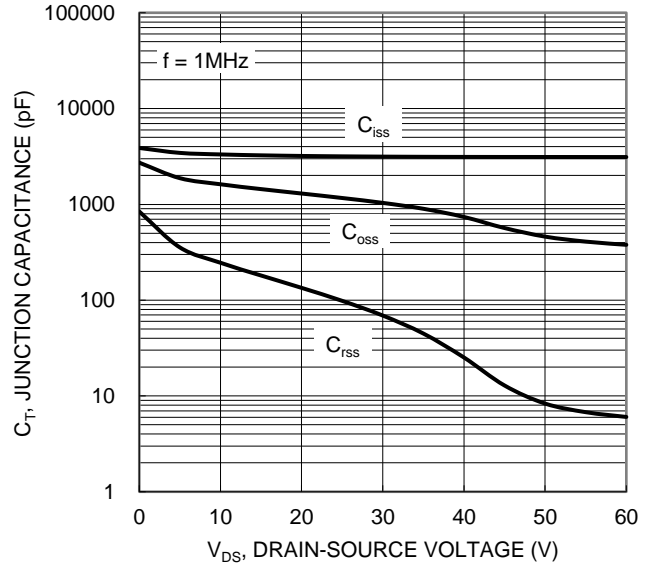


Figure 10. Typical Junction Capacitance

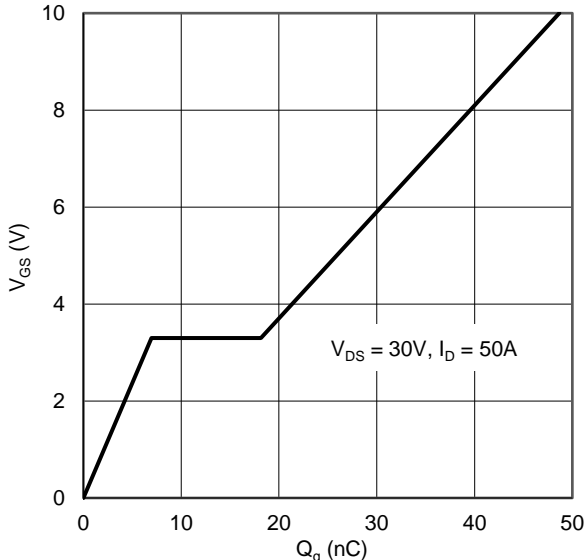


Figure 11. Gate Charge

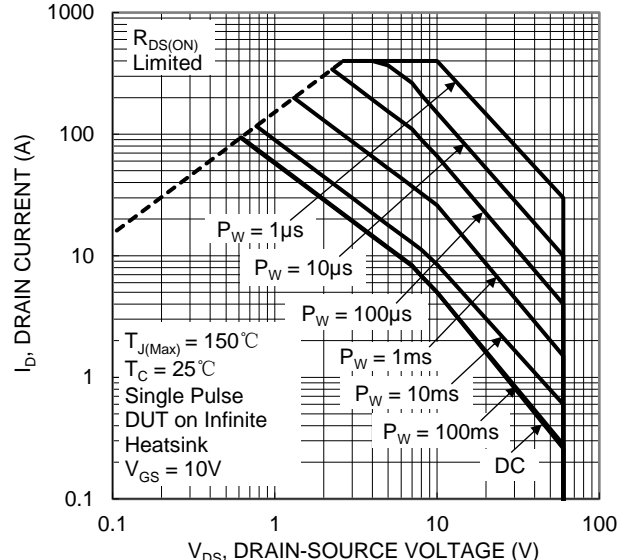


Figure 12. SOA, Safe Operation Area

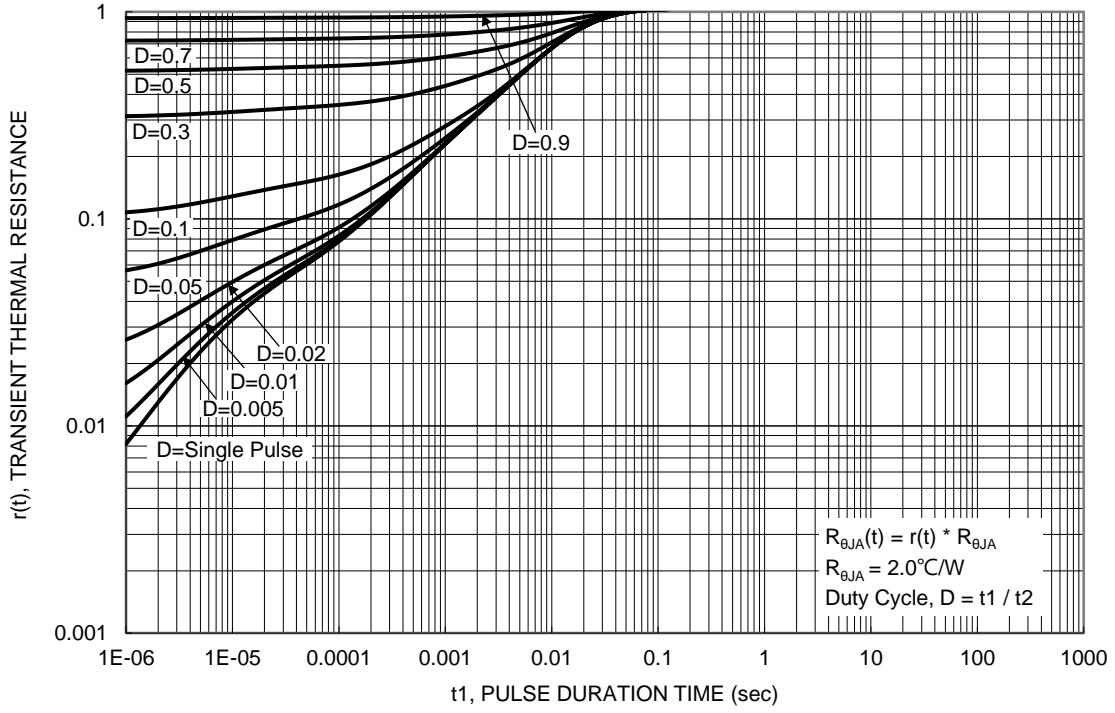
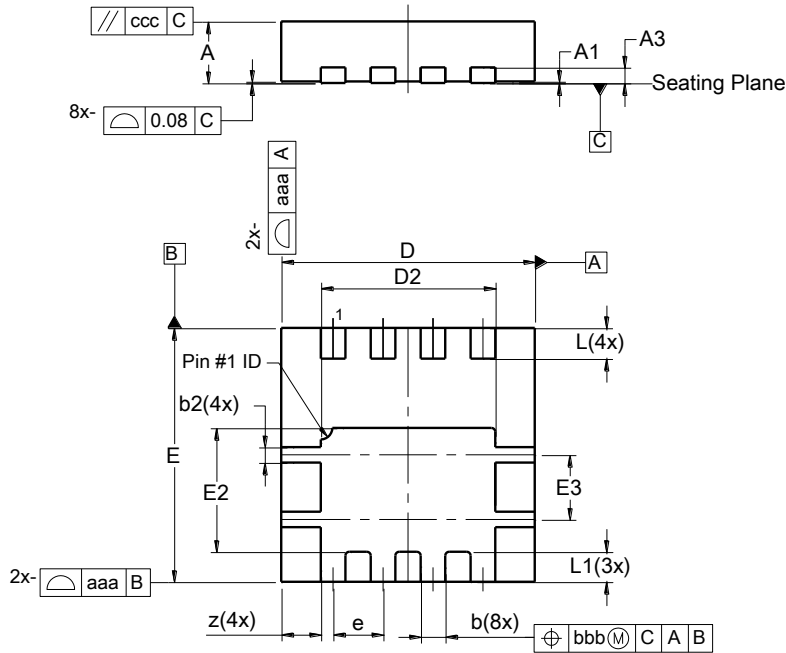


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**

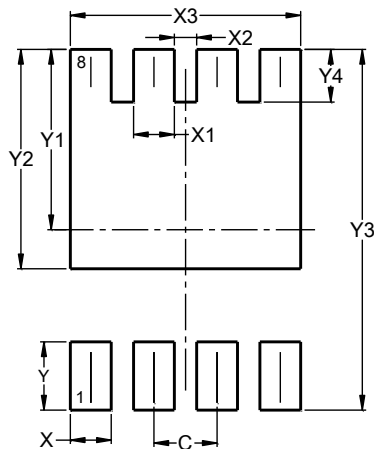


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
aaa	0.25		
bbb	0.10		
ccc	0.10		
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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